Amendments to the Claims:

The listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

5   1. (Currently Amended) A method of forming storage nodes in a dynamic random access memory (DRAM) on a semiconductor wafer, the semiconductor wafer comprising a substrate, a thin film layer positioned on the substrate, and a photoresist layer positioned on the thin film layer, the method comprising:

10   performing a first exposure process to form first exposure regions that are lines parallel with each other and separated by unexposed parallel lines on the photoresist layer;

          performing a second exposure process to form second exposure regions on the photoresist layer that cut the unexposed parallel lines are

15   rectangles interlaced with and perpendicular to each other on the photoresist layer, and the second exposure regions doing not do not overlap the first exposure regions;

          performing a development process on the first exposure regions and the second exposure regions of the photoresist layer;

20   removing the first exposure regions and the second exposure regions of the photoresist layer to form an array photoresist layer on the thin film layer; and

          using the array photoresist layer as a mask to perform an etching process to remove portions of the thin film layer not covered by the

25   array photoresist layer so as to form an array thin film layer, the array thin film layer being used as the storage nodes in the DRAM.

          2. (Original) The method of claim 1 wherein the method is used to prevent rounding corner effects, end-of-line shortening, or other optical

proximity effects to patterns of the photoresist layer.

3-6. (cancelled)